L Number	Hits	Search Text	DB	Time stamp
15	4	(US-5423944-\$ or US-6326218-\$ or	USPAT;	2003/06/18
	'	US-6451665-\$).did. or (EP-782177-\$).did.	EPO	15:11
34	5	(US-6326218-\$ or US-6432835-\$ or	USPAT	2003/06/18
		US-6451665-\$ or US-6506636-\$ or		15:11
3.5		US-6512182-\$).did.		
35	7	((12 22222 4 22 22 232222 4 22	USPAT;	2003/06/18
		US-6451665-\$ or US-6506636-\$ or US-6512182-\$).did.) or ((US-5423944-\$ or	EPO; JPO	15:12
		US-6326218-\$ or US-6451665-\$).did. or		
		(EP-782177-\$).did.)		
36	3		USPAT;	2003/06/18
		US-6451665-\$ or US-6506636-\$ or	EPO; JPO	15:14
		US-6512182-\$).did.) or ((US-5423944-\$ or		
		US-6326218-\$ or US-6451665-\$).did. or (EP-782177-\$).did.)) and wet adj3		
		(etch\$3)		
37	353394		USPAT;	2003/06/18
	1	palladium pd iridium ir	EPO; JPO	15:13
38	5006	(Paradam Prantitional and Endurant In	USPAT;	2003/06/18 ,
		palladium pd iridium ir ) and wet adj3	EPO; JPO	15:14
39	918	(etch\$3) ((platinum pt ruthenium ru rhodium rh	IICDA TI	2002/05/20
33	910	palladium pd iridium ir ) and wet adj3	USPAT; EPO; JPO	2003/06/18 15:17
		(etch\$3)) and (NaCl "sodium chloride" KCl	EFO, OFO	13.17
		"potassium chloride" CaCl "calcium		
		chloride" HCl "hydrochloric acid" "liquid		
40	320985	salt")		
40	320963	NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl	USPAT; EPO; JPO	2003/06/18 15:18
		"hydrochloric acid" "liquid salt"	EPO, 0PO	15:10
41	31912		USPAT;	2003/06/18
		chloride" CaCl "calcium chloride" HCl	EPO; JPO	15:18
		"hydrochloric acid" "liquid salt") same		
		(platinum pt ruthenium ru rhodium rh palladium pd iridium ir )		
42	4783		USPAT;	2003/06/18
		chloride" CaCl "calcium chloride" HCl	EPO; JPO	15:21
		"hydrochloric acid" "liquid salt") adj10		
		(platinum pt ruthenium ru rhodium rh		
43	4	palladium pd iridium ir )		
43	4	(NaCl "sodium chloride" KCl "potassium chloride" CaCl "calcium chloride" HCl	USPAT; EPO; JPO	2003/06/18
		"hydrochloric acid" "liquid salt") adj10	EPO, JPO	15:22
		(platinum pt ruthenium ru rhodium rh		
		palladium pd iridium ir ) adj15 (wet adj3		
4.4		etch\$3)		
44	65	(wet adj3 etch\$3) adj5 (platinum pt ruthenium ru rhodium rh palladium pd	USPAT;	2003/06/18
		iridium ir )	EPO; JPO	16:17
45	1	5515984.pn.	USPAT;	2003/06/18
	[	-	EPO; JPO	15:30
46	0	(wet adj3 etch\$3) adj5 "noble metals"	USPAT;	2003/06/18
47		(otahéa) adik "mahla	EPO; JPO	16:18
3'	56	(etch\$3) adj5 "noble metals"	USPAT; EPO; JPO	2003/06/18
_	294959	capacitor	USPAT;	2003/06/17
			EPO; JPO	18:25
-	353394	platinum pt ruthenium ru rhodium rh	USPAT;	2003/06/18
_ !	12200	palladium pd iridium ir	EPO; JPO	15:13
-	12300	(O3 ozone) and (water steam H2O) and (halgenide Fluoride Chloride Bromide	USPAT;	2003/06/17
		iodide)	EPO; JPO	18:28
-	448	(03 ozone) and (water steam H2O) and	USPAT;	2003/06/17
		(halgenide Fluoride Chloride Bromide	EPO; JPO	18:39
		iodide) same (etch etching etcher		
_	20324	etchant)	110 D.T	2002/05/55
	20324	capacitor and (platinum pt ruthenium ru rhodium rh palladium pd iridium ir)	USPAT; EPO; JPO	2003/06/17 18:29
		Parameter Pre 221414411 111	210, OFO	

-	44	(capacitor and (platinum pt ruthenium ru	USPAT;	2003/06/18
		rhodium rh palladium pd iridium ir)) and	EPO; JPO	15:12
		((O3 ozone) and (water steam H2O) and	,	
		(halgenide Fluoride Chloride Bromide		
	1	iodide) same (etch etching etcher		
	l	etchant))		
-	27	1 (00 020:10) banke (water becam 1120) same	USPAT;	2003/06/17
		(halgenide Fluoride Chloride Bromide	EPO; JPO	18:48
		iodide halogen F2 Cl2 Br2 I2) same (etch		
		etching etcher etchant)	ĺ	
-	6	8-153707	USPAT	2003/06/18
				12:18
-	0	8-153707	JPO	2003/06/18
				12:20
-	0	08-153707	JPO	2003/06/18
		"00 45000"		12:20
_	0	"08-153707"	JPO	2003/06/18
				12:20
-	0	"manufacturing method for semiconductor	JPO	2003/06/18
_	1	device".ti.		12:21
_	0	"manufacturing method for semiconductor device"	JPO	2003/06/18
_	178515		i	12:21
_	1/0313	takeshi.inv.	JPO	2003/06/18
_	121	tokoohi ima and Buthania		12:21
	121	takeshi.inv. and Ruthenium	JPO	2003/06/18
_	1	(takoghi ing and Buthamiam) 1 aan		12:21
	1	(takeshi.inv. and Ruthenium) and SOG	JPO	2003/06/18
	<u> </u>			12:22